

## E Series Power MOSFET

### DESCRIPTION

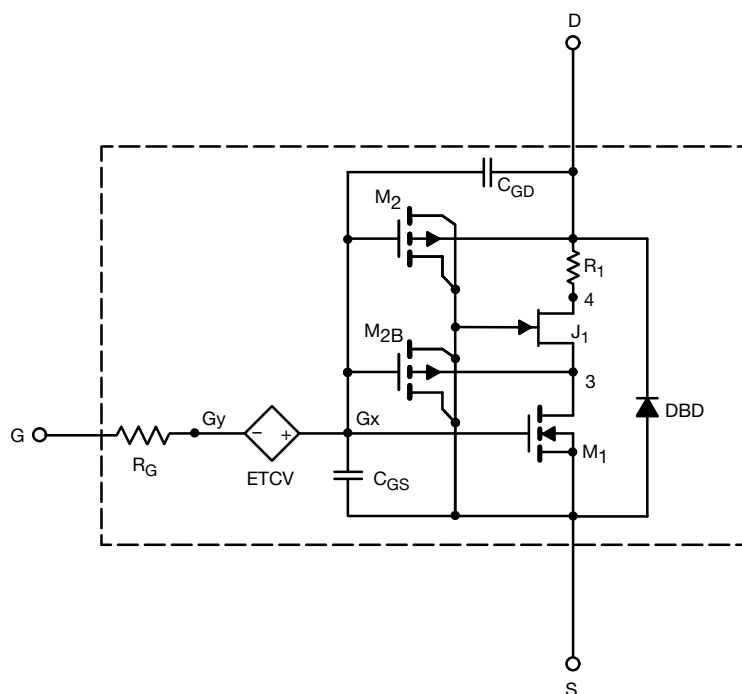
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over 25 °C to 150 °C temperature ranges under the pulsed 0 V to 15 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

### CHARACTERISTICS

- N-channel vertical DMOS
- Macro model (subcircuit model)
- Level 3 MOS
- Apply for both linear and switching application
- Accurate over 25 °C to 150 °C temperature range
- Model the gate charge

### SUBCIRCUIT MODEL SCHEMATIC



### Note

- This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits



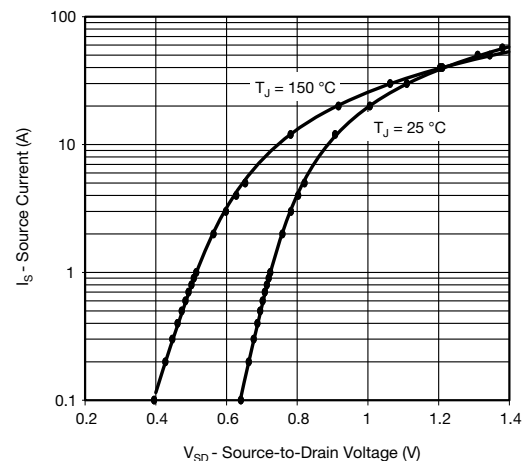
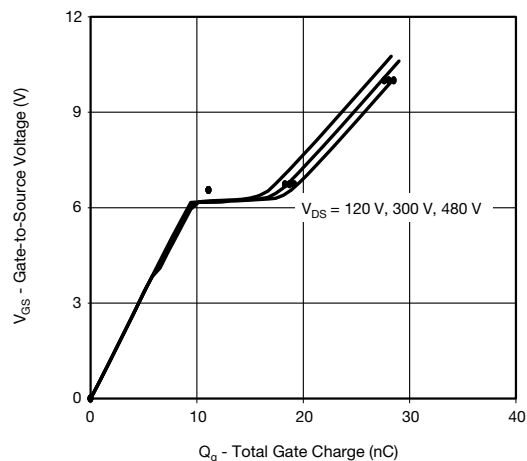
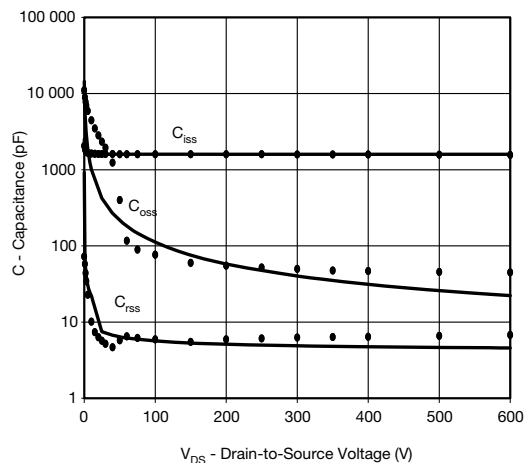
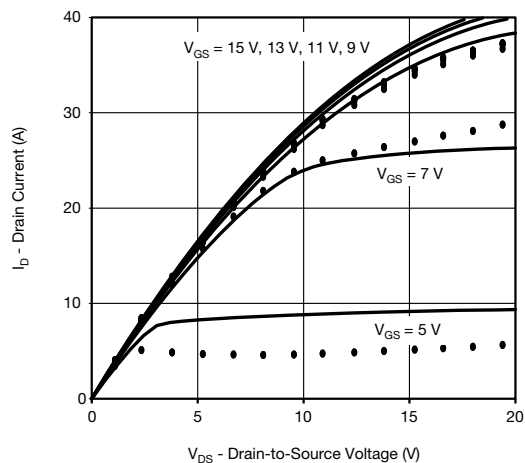
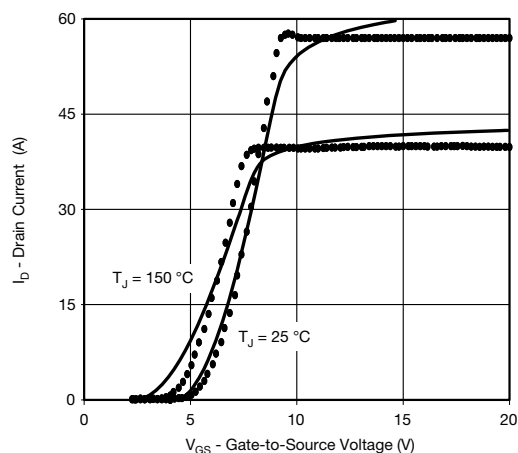
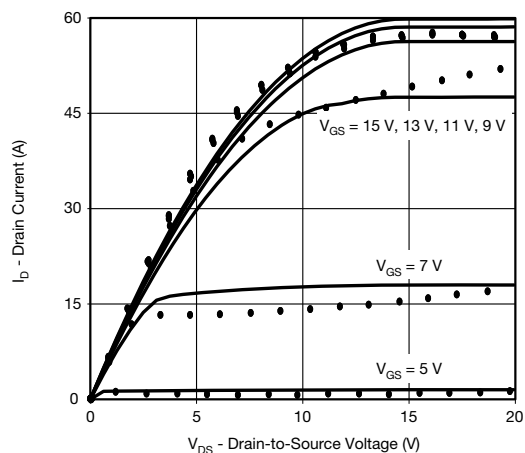
SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	4	-	V
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 12 A	0.140	0.106	Ω
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 20 V, I <sub>D</sub> = 12 A	10	6.9	S
Dynamic <sup>b</sup>					
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, f = 1 MHz	1600	1600	pF
Output Capacitance	C <sub>oss</sub>		105	76	
Reverse Transfer Capacitance	C <sub>rss</sub>		6	6	
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 480 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 12 A	29	29	nC
Gate-Source Charge	Q <sub>gs</sub>		10	11	
Gate-Drain Charge	Q <sub>gd</sub>		8	8	
Drain-Source Body Diode Characteristics					
Diode Forward Voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub> = 12 A, V <sub>GS</sub> = 0 V	0.9	-	V
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C, I <sub>F</sub> = I <sub>S</sub> = 12 A, di/dt = 100 A/μs, V <sub>R</sub> = 400 V	360	343	ns
Reverse Recovery Charge	Q <sub>rr</sub>		6	5.6	μC

**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
b. Guaranteed by design, not subject to production testing



## COMPARISON OF MODEL WITH MEASURED DATA ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)



### Note

- Dots and squares represent measured data

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